

November 1997

### Features

- Typical Propagation Delay (A to B, B to A) of 7ns at  $V_{CC} = 5V$ ,  $C_L = 15pF$ ,  $T_A = 25^\circ C$
- Three-State Outputs
- Buffered Inputs
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . .  $-55^\circ C$  to  $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$  at  $V_{CC} = 5V$
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,  $V_{IL} = 0.8V$  (Max),  $V_{IH} = 2V$  (Min)
  - CMOS Input Compatibility,  $I_I \leq 1\mu A$  at  $V_{OL}$ ,  $V_{OH}$

### Description

The Harris CD74HCT242, CD74HC243 and CD74HCT243 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads.

The CD74HCT242 is an inverting buffer; the CD74HC243 and CD74HCT243 are non-inverting buffers.

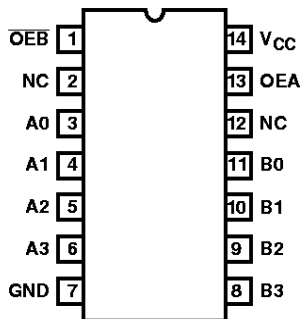
The states of the output enables ( $\overline{OEB}$ ,  $OEA$ ) determine both the direction of flow (A to B, B to A), and the three-state mode.

### Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC243E	-55 to 125	14 Ld PDIP	E14.3
CD74HC243M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT243M	-55 to 125	14 Ld SOIC	M14.15

### Pinout

CD74HCT242, CD74HC243, CD74HCT243  
(PDIP, SOIC)  
TOP VIEW

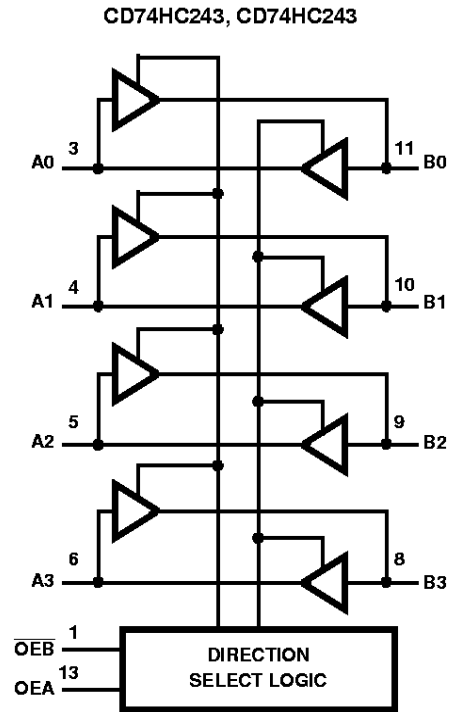
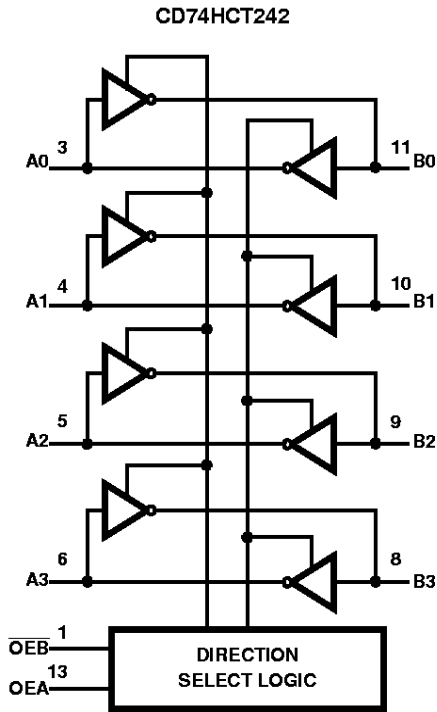


### NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales

CD74HCT242, CD74HC243, CD74HCT243

Functional Diagrams



TRUTH TABLE

CONTROL INPUTS		HCT242 SERIES		HC, HCT243 SERIES	
		DATA PORT STATUS		DATA PORT STATUS	
$\overline{OEB}$	OEA	An	Bn	An	Bn
H	H	$\overline{O}$	I	O	I
L	H	Z	Z	Z	Z
H	L	Z	Z	Z	Z
L	L	I	$\overline{O}$	I	O

NOTE:

H = High Voltage Level

L = Low Voltage Level

I = Input

O = Output (Same Level as Input)

$\overline{O}$  = Output (Inversion of Input Level)

Z = High Impedance

To prevent excess currents in the High Z modes all I/O terminals should be terminated with 10kΩ to 1MΩ resistors.

# CD74HCT242, CD74HC243, CD74HCT243

## Absolute Maximum Ratings

DC Supply Voltage, $V_{CC}$ .....	-0.5V to 7V
DC Input Diode Current, $I_{IK}$	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Output Diode Current, $I_{OK}$	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Drain Current, per Output, $I_O$	
For $-0.5V < V_O < V_{CC} + 0.5V$ .....	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, $I_O$	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ .....	$\pm 25mA$
DC $V_{CC}$ or Ground Current, $I_{CC}$ .....	$\pm 70mA$

## Thermal Information

Thermal Resistance (Typical, Note 3)	$\theta_{JA}$ ( $^{\circ}C/W$ )
PDIP Package .....	90
SOIC Package .....	175
Maximum Junction Temperature .....	$150^{\circ}C$
Maximum Storage Temperature Range .....	$-65^{\circ}C$ to $150^{\circ}C$
Maximum Lead Temperature (Soldering 10s) .....	$300^{\circ}C$
(SOIC - Lead Tips Only)	

## Operating Conditions

Temperature Range ( $T_A$ ) .....	$-55^{\circ}C$ to $125^{\circ}C$
Supply Voltage Range, $V_{CC}$	
HC Types .....	2V to 6V
HCT Types .....	4.5V to 5.5V
DC Input or Output Voltage, $V_I$ , $V_O$ .....	0V to $V_{CC}$
Input Rise and Fall Time	
2V .....	1000ns (Max)
4.5V .....	500ns (Max)
6V .....	400ns (Max)

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

### NOTE:

- $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

## DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS			25 $^{\circ}C$			-40 $^{\circ}C$ TO 85 $^{\circ}C$		-55 $^{\circ}C$ TO 125 $^{\circ}C$		UNITS
		$V_I$ (V)	$I_O$ (mA)	$V_{CC}$ (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>												
High Level Input Voltage	$V_{IH}$	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	$V_{IL}$	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V

**CD74HCT242, CD74HC243, CD74HCT243**

**DC Electrical Specifications (Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> or GND	-	6	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	-	6	-	-	±0.5	-	±0.5	-	±10	μA
<b>HCT TYPES</b>												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI <sub>CC</sub>	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	-	5.5	-	-	±0.5	-	±5.0	-	±10	μA

NOTE:

4. For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

**HCT Input Loading Table**

INPUT	UNIT LOADS
An, Bn	1.1
OEA, $\overline{OEB}$	0.6

NOTE: Unit Load is ΔI<sub>CC</sub> limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

**CD74HCT242, CD74HC243, CD74HCT243**

**Switching Specifications** Input  $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	$V_{CC}$ (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
<b>HC TYPES</b>								
Propagation Delay Data to Outputs (HC243)	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	2	-	90	115	135	ns
			4.5	-	18	23	27	ns
		$C_L = 15\text{pF}$	5	7	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	15	20	23	ns
Output High-Z, to High Level to Low Level	$t_{PZL}, t_{PZH}$	$C_L = 50\text{pF}$	2	-	150	190	225	ns
		$C_L = 50\text{pF}$	4.5	-	30	38	45	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	26	33	38	ns
Output High Level, Output Low Level to High-Z	$t_{PHZ}, t_{PLZ}$	$C_L = 50\text{pF}$	2	-	150	190	225	ns
		$C_L = 50\text{pF}$	4.5	-	30	38	45	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	26	33	38	ns
Output Transition Times	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	$C_I$	-	-	-	10	10	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	20	20	20	pF
Power Dissipation Capacitance (HC243) (Notes 5, 6)	$C_{PD}$	-	5	80	-	-	-	pF
<b>HCT TYPES</b>								
Propagation Delay Data to Outputs (HCT242)	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	20	25	30	ns
		$C_L = 15\text{pF}$	5	8	-	-	-	ns
Propagation Delay Data to Outputs (HCT243)	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	22	28	33	ns
		$C_L = 15\text{pF}$	5	9	-	-	-	ns
Output High-Z to High Level to Low Level	$t_{PZH}, t_{PZL}$	$C_L = 50\text{pF}$	4.5	-	34	43	51	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output High Level, Output Low Level to High-Z	$t_{PHZ}, t_{PLZ}$	$C_L = 50\text{pF}$	4.5	-	35	44	53	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output Transition Times	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	4.5	-	12	15	18	ns
Input Capacitance	$C_I$	-	-	-	10	10	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	$C_{PD}$	HCT242	5	90	-	-	-	pF
		HCT243	5	91	-	-	-	pF

**NOTES:**

- $C_{PD}$  is used to determine the dynamic power consumption, per channel.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $f_o$  = Output Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

Test Circuits and Waveforms

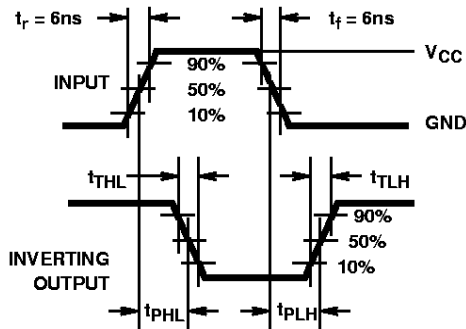


FIGURE 1. HC AND HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

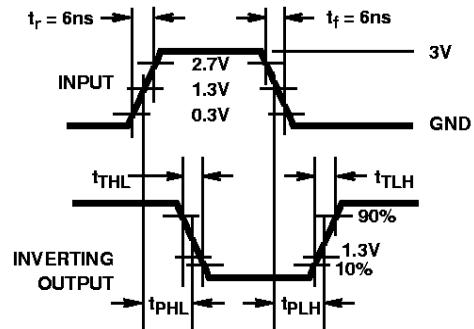


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

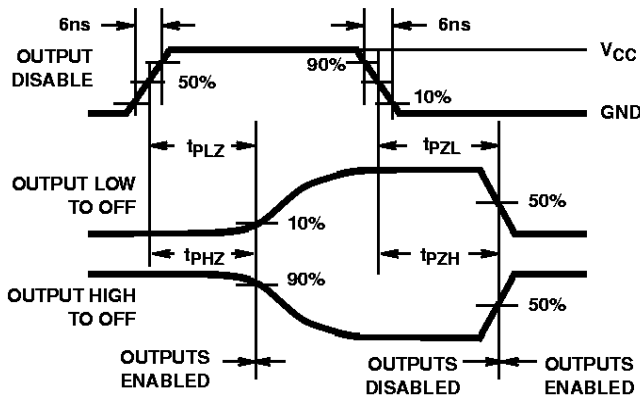


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

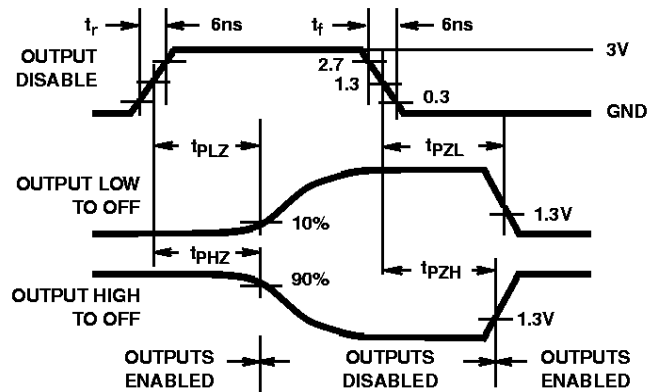
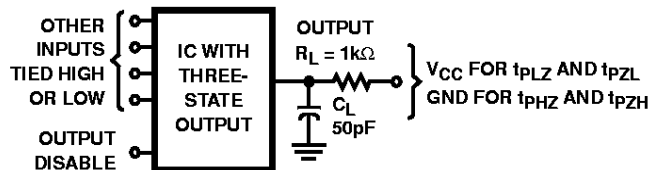


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms  $t_{pLZ}$  and  $t_{pZL}$  are the same as those for three-state shown on the left. The test circuit is Output  $R_L = 1k\Omega$  to  $V_{CC}$ ,  $C_L = 50pF$ .

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT